



LGAD development and its application for X-ray detection

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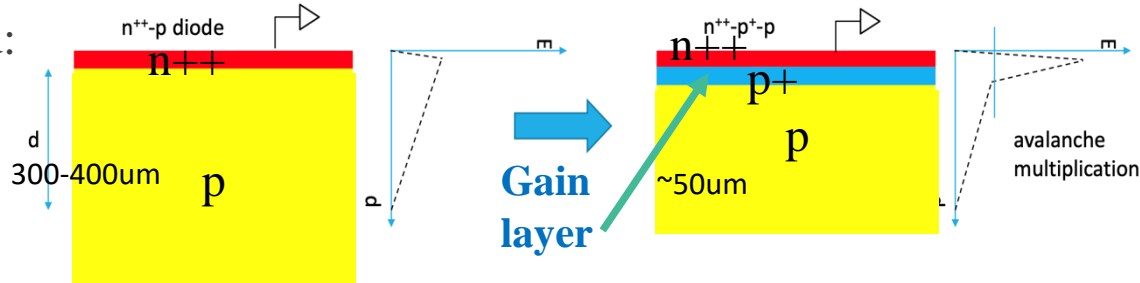


LGAD detector

➤ **Low Gain Avalanche Detectors (LGAD)** is a silicon detector technology that has timing resolution <35ps.

➤ Compared with PIN, a gain layer between P and N++ is added:

- Work in a linear mode, Gain:10~50
- **Good Signal/Noise ratio** without self triggering
- Thin depleted region to decrease t_{rise} (fast timing)
- Types of LGAD: DC-LGAD, AC-LGAD, Ti-LGAD
Inversed LGAD, Monolithic LGAD...



➤ Owing to its good performance, LGAD technology is chosen as timing detector for ATLAS HGTD and CMS ETL project.

➤ And have good potential for other applications(future collider, X-ray detection, iCT etc)

$$\sigma_j = \frac{\sigma_n}{\left| \frac{dV}{dt} \right|} = \frac{\sigma_n}{\left| \frac{S}{t_r} \right|} = \frac{t_r}{\left| \frac{S}{\sigma_n} \right|}$$

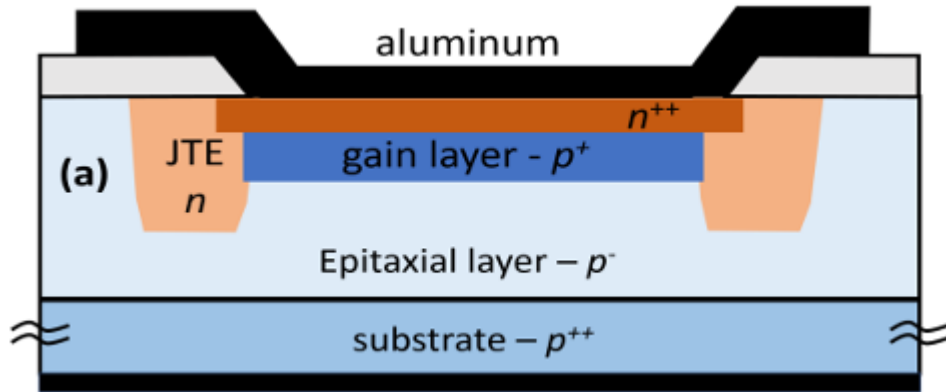
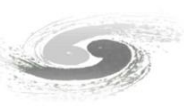
Size of noise

Slope of vol.

Size of signal

Ramping time

Types of LGAD



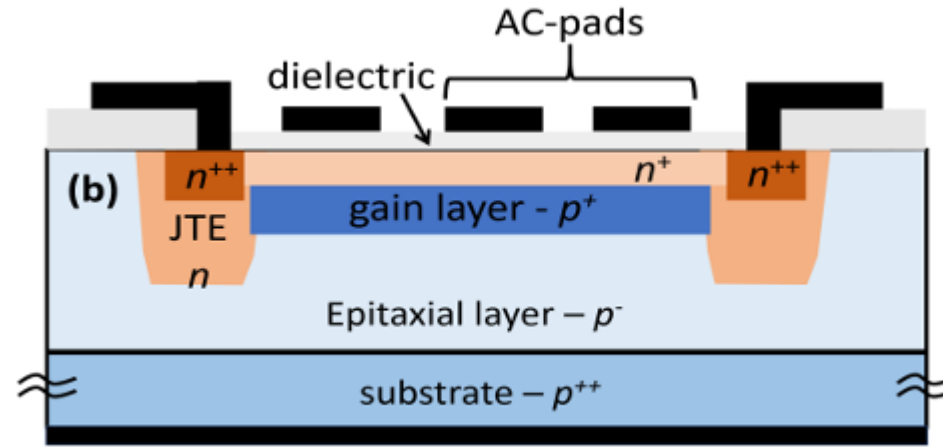
DC-LGAD

- The read-out electrode is placed and connected to the N++ layer.
- Large pixel size and dead zone between pixels (JTE, Pstop)

Timing performance: <35ps

Position resolution: pixel size/ $\sqrt{12}$
1.3mm/ $\sqrt{12}$

Dead area: JTE, P-stop



AC-LGAD

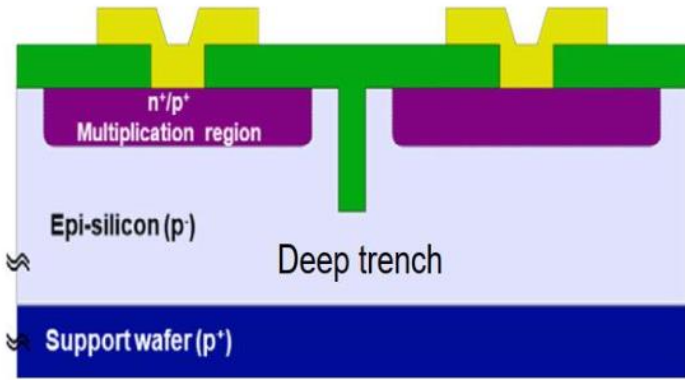
- metal AC readout electrode and a thin dielectric layer (Si_3N_4 , SiO_2) above the N+ layer
- **Less dead area and better position resolution**

AC-coupled LGADs, n++ implant well is replaced by a more resistive n+ layer, with electrodes that are AC coupled to it via a thin dielectric layer

- Research institute: FBK, HPK, INFN, BNL, CNM, USTC, IHEP...



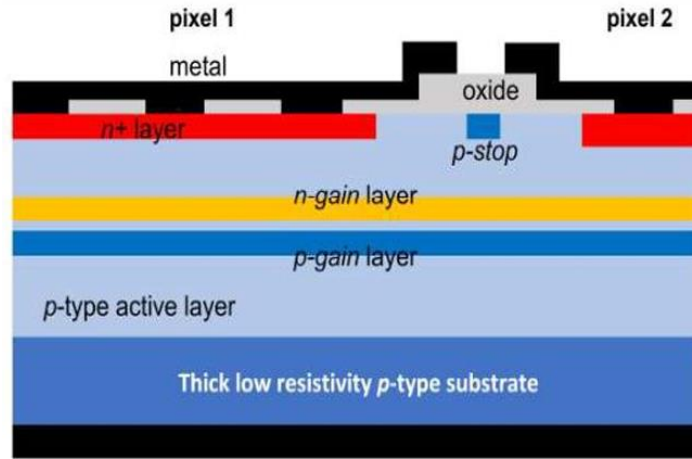
Types of LGAD



Ti-LGAD

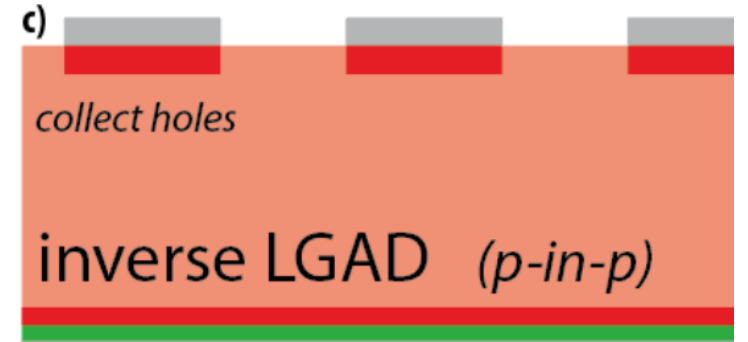
- isolation structures (p-stop and JTE) are replaced by a deep trench, less than a μm wide
- Increasing the fill factor

Monolithic LGAD



DJ-LGAD

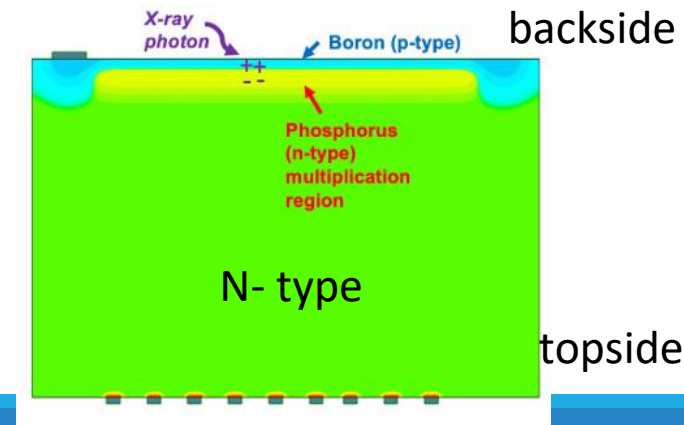
- A deep junction be made by a large area of uniform n+ and p+ gain implants. and n+ DC coupled electrodes are placed a few microns from the surface.
- To increase fill factor and improve radiation hardness



Gain layer

- inverse-LGAD to increase fill factor

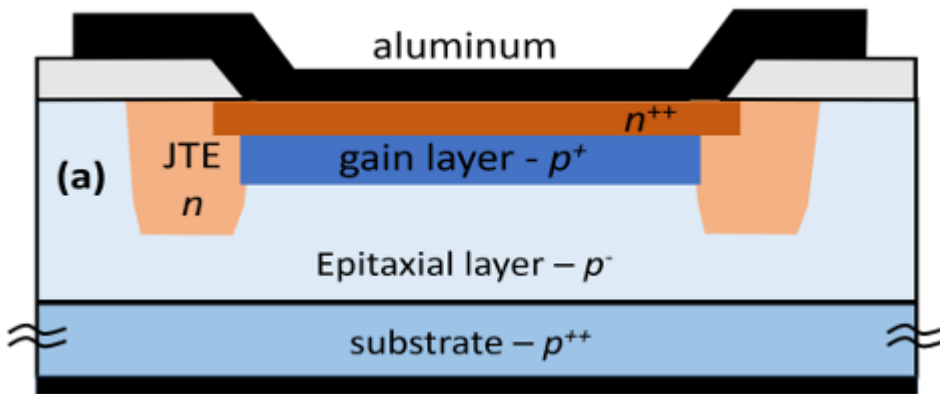
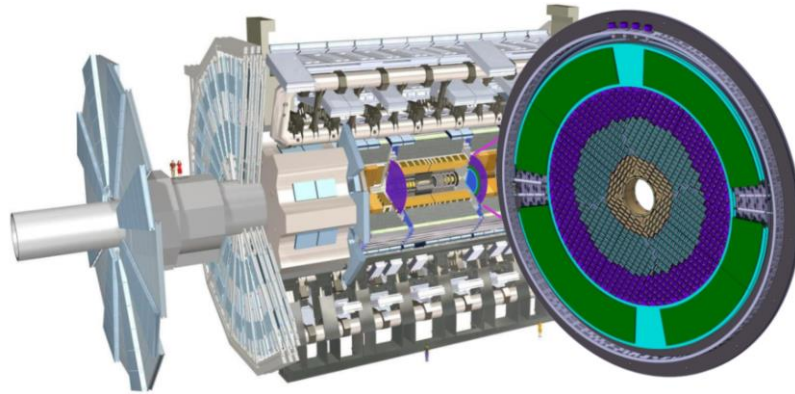
Thin Entrance Window LGADs
For soft X-rays with energies as low as 250 eV





DC-LGAD development

For ATLAS HL-LHC upgrades
ATLAS High Granularity Timing Detector (HGTD)



➤ to provide precise timing information to mitigate pile-up in HL-LHC.

➤ ~21,000 LGAD sensors for HGTD project

➤ Requirements:

• Size: 15x15 array, 1.3x1.3 mm² pixel size

• Active thickness: 50 um (Thin: faster rise time, lower impact from radiation)

• **LGAD sensor can withstand the lifetime of the HL-LHC running: irradiation requirement**

Maximum n_{eq} fluences: $2.5 \times 10^{15} n_{eq}/cm^2$

Total Ionizing Dose (TID): 2 MGy at the end of HL-LHC (4000 fb⁻¹)

• Time resolution: 35 ps (start), 70 ps (end) per hit, while 30 ps (start), 50 ps (end) per track

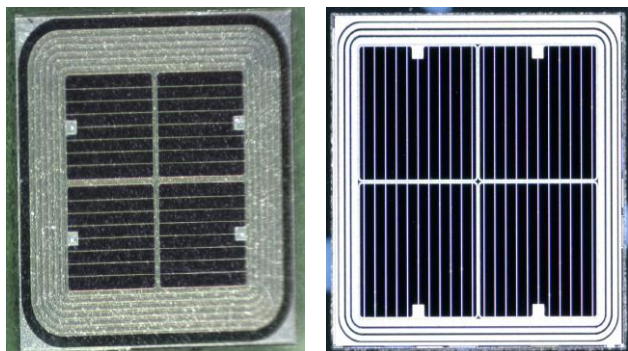
• Collected charge per hit >4 fC (minimum charge needed by the ASIC to hold good time resolution)

• Hit efficiencies of 97% (95%) at the start (end) of their lifetime

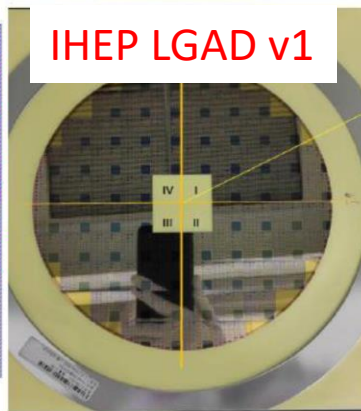
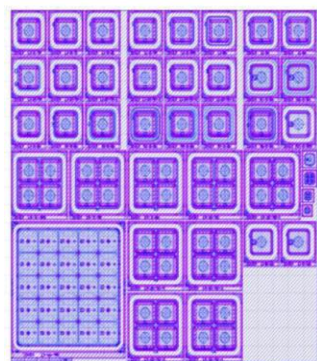


LGAD Development at IHEP

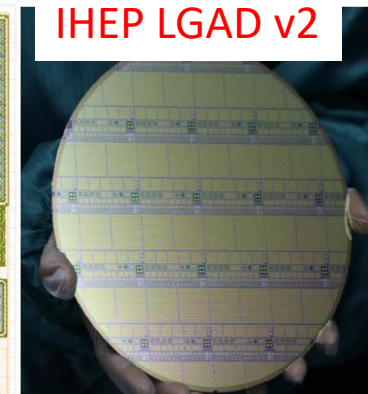
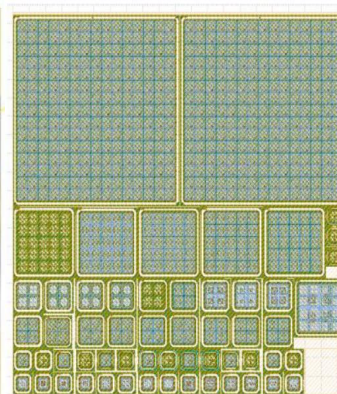
IHEP-NDL(2019)



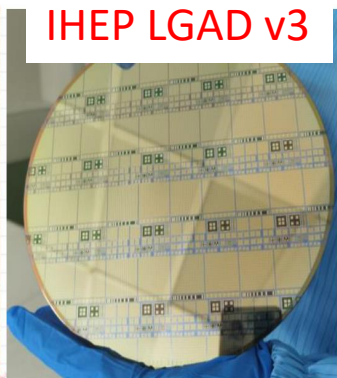
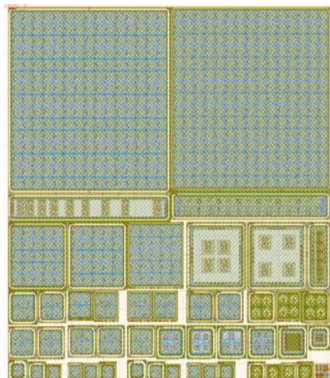
IHEP LGAD v1 (2020.9)



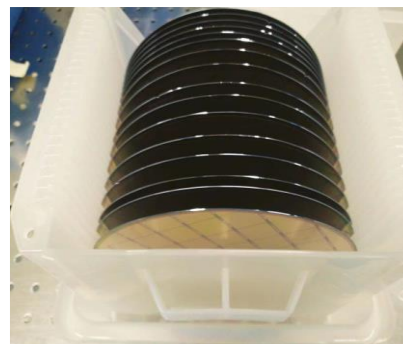
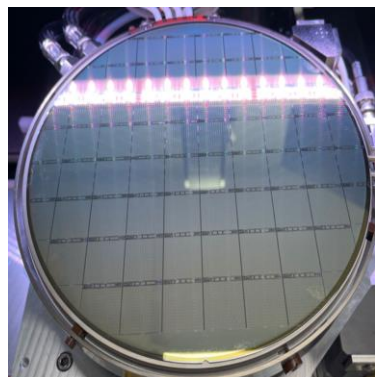
IHEP LGAD v2 (2021.6)



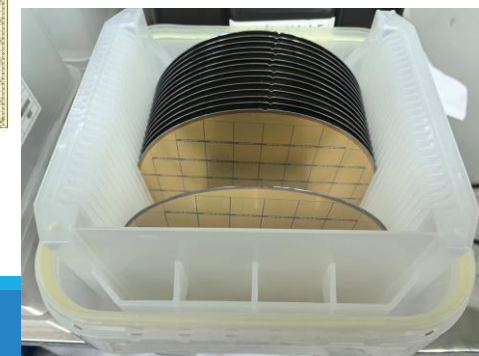
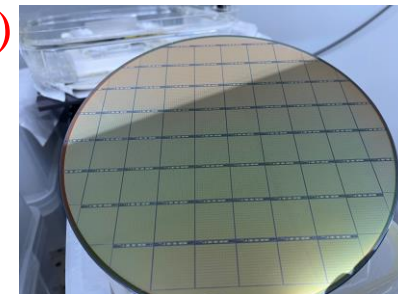
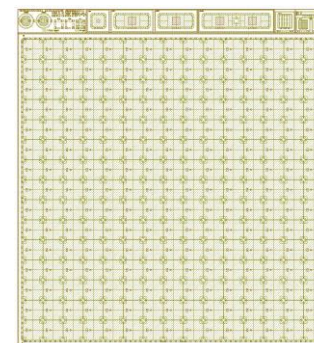
IHEP LGAD v3 (2022.5)



Pre-production for ATLAS (2023.7)



Mass production for ATLAS (2024.8)



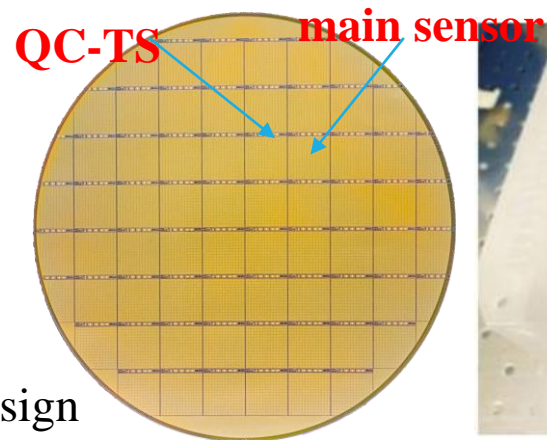


For ATLAS HGTD

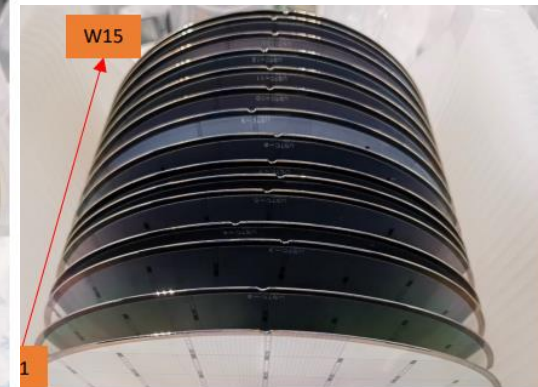
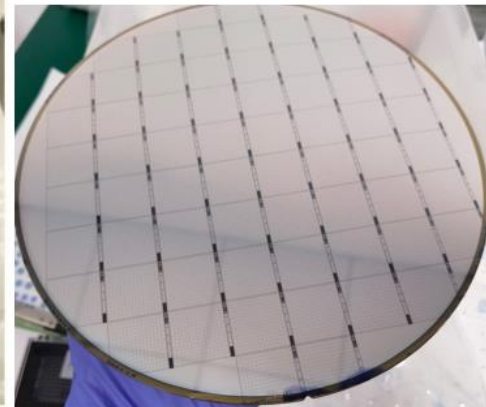
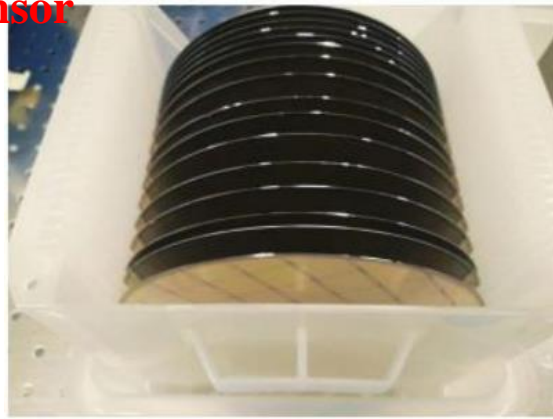
- LGAD sensors for HGTD project: ~21,000
 - IHEP design: 90%
 - USTC design: 10%
- In 2023, IHEP design LGAD sensors be selected in the HGTD sensor tendering process.
- Pre-production started at June 2023. Sensor pre-productions finished in 2023 – produced comfortably enough sensors for HGTD needs.
- HGTD group testing results show that the IHEP and USTC sensors properties fulfill HGTD specification.
- PRR passed at July 2024, and final production started after it. Some wafers (~20) already be fabricated.

vendor		Percent
IHEP design	CERN	54%
	China in-kind	24%
	Spain in-kind	12%
USTC design	China in-kind	10%

	Wafer number	Good sensors
IHEP design	58	~1,700
USTC design	9	~200



IHEP design



USTC design



For ATLAS HGTD

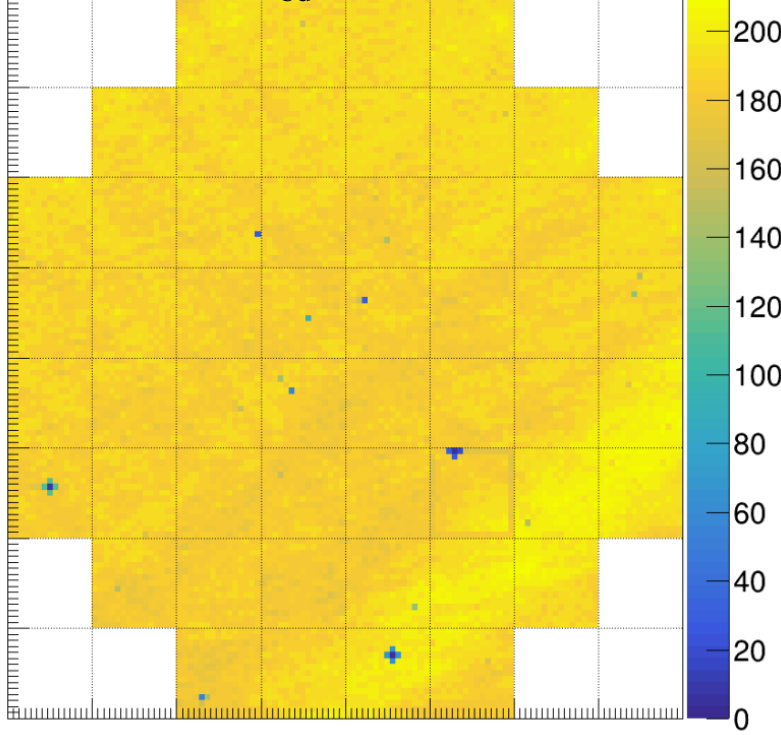
➤ The 15x15 array sensors have good IV performance and uniformity

Breakdown voltage deviation for 225 pads is less than 5% : $RMS(V_{bd,pad}) / \langle V_{bd,pad} \rangle < 5\%$

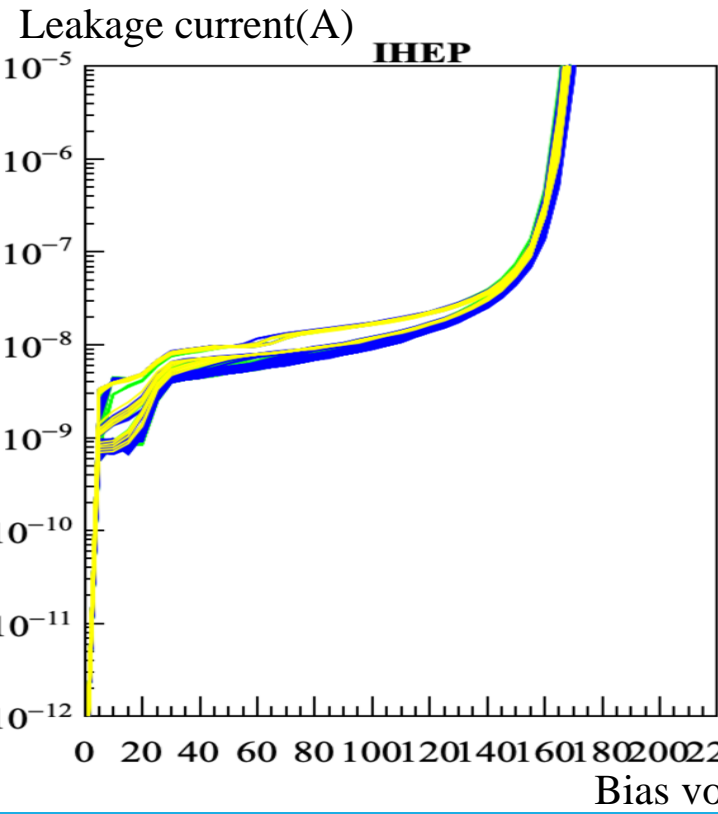
The ratio of the maximum and minimum leakage current is less than 3 (Pad leakage current spread at $0.8V_{bd}$), peak to peak within a factor of 3X.

➤ Yield: pad yield: >99%, sensor yield: ~64%

Mapping of V_{bd} of sensors on one wafer

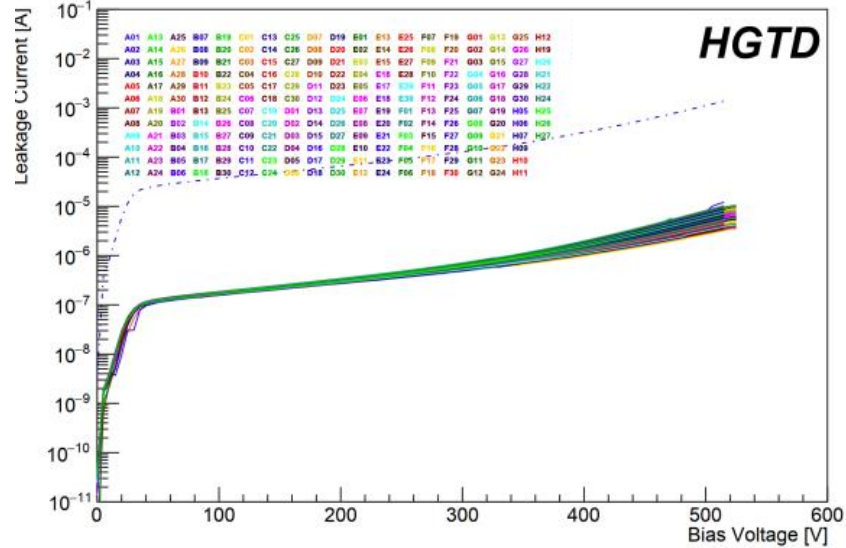


V_{BD} Map

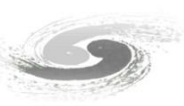


Good IV uniformity before and after irradiation

IHEP LGAD sensors after $2.5e15 n_{eq}/cm^2$



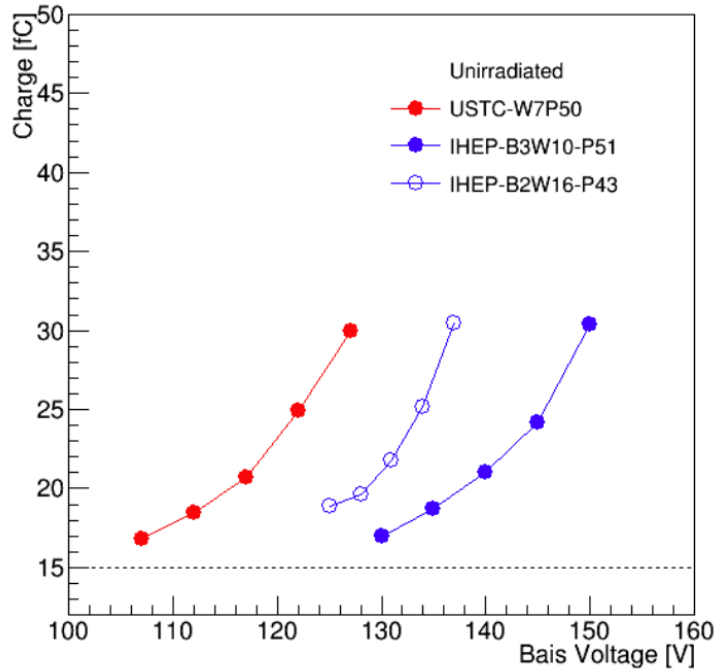
For ATLAS HGTD



Performance of pre-production sensors: Beam test results

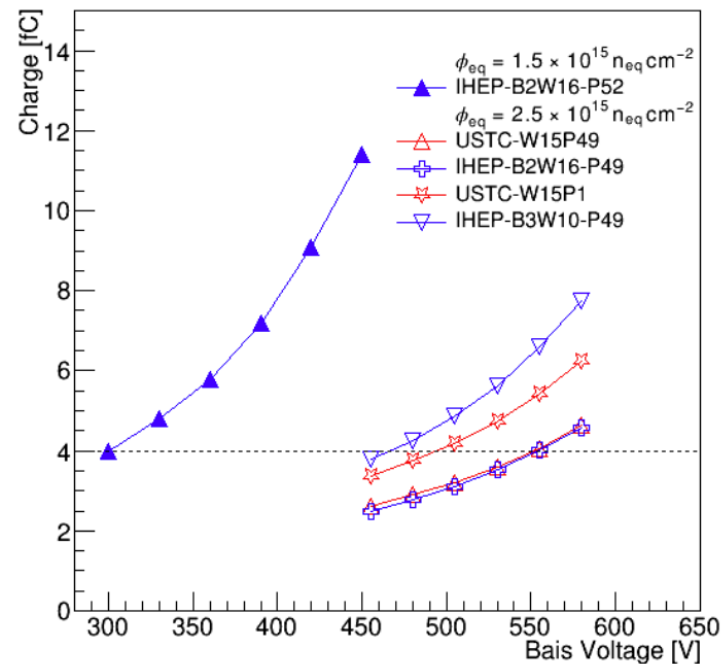
- **Collected charge:** The sensors can collect more than 15 fC charge before irradiation and >4 fC charge after irradiation at bias voltage <550 V (SEB limit)
- **Timing resolution:** The timing resolution is better than 35 ps (50 ps) before(after) irradiation (fluence $2.5 \times 10^{15} \text{ n}_{\text{eq}}/\text{cm}^2$)
- The collected charge and timing performance of sensors from pre-production fulfills HGTD requirement.

Collected Charge - HGTD TB June 2024



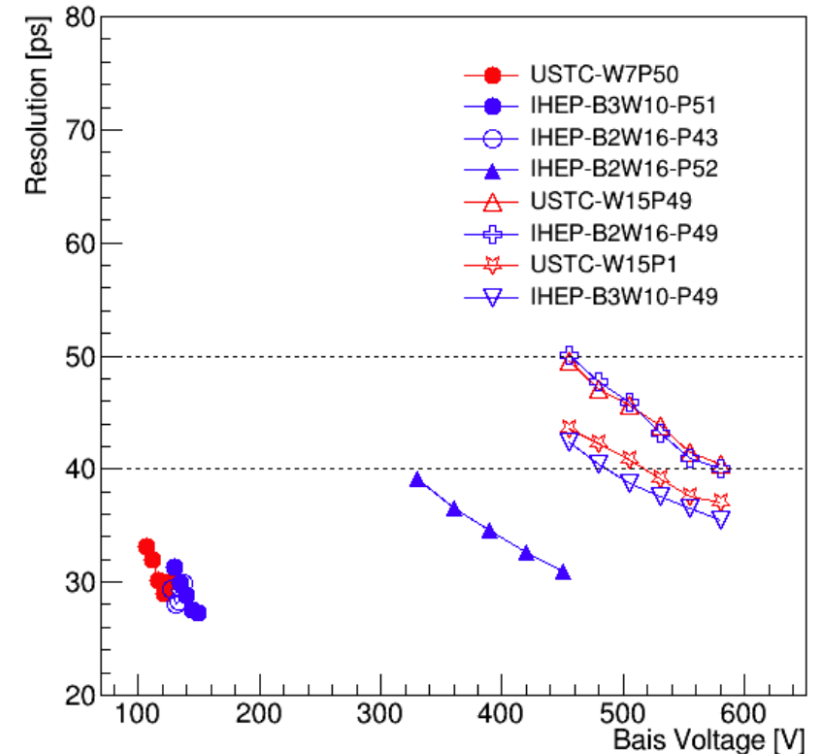
unirradiated sensor

Collected Charge - HGTD TB June 2024

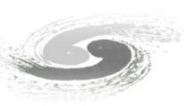


irradiated sensor

Time Resolution - HGTD TB June 2024

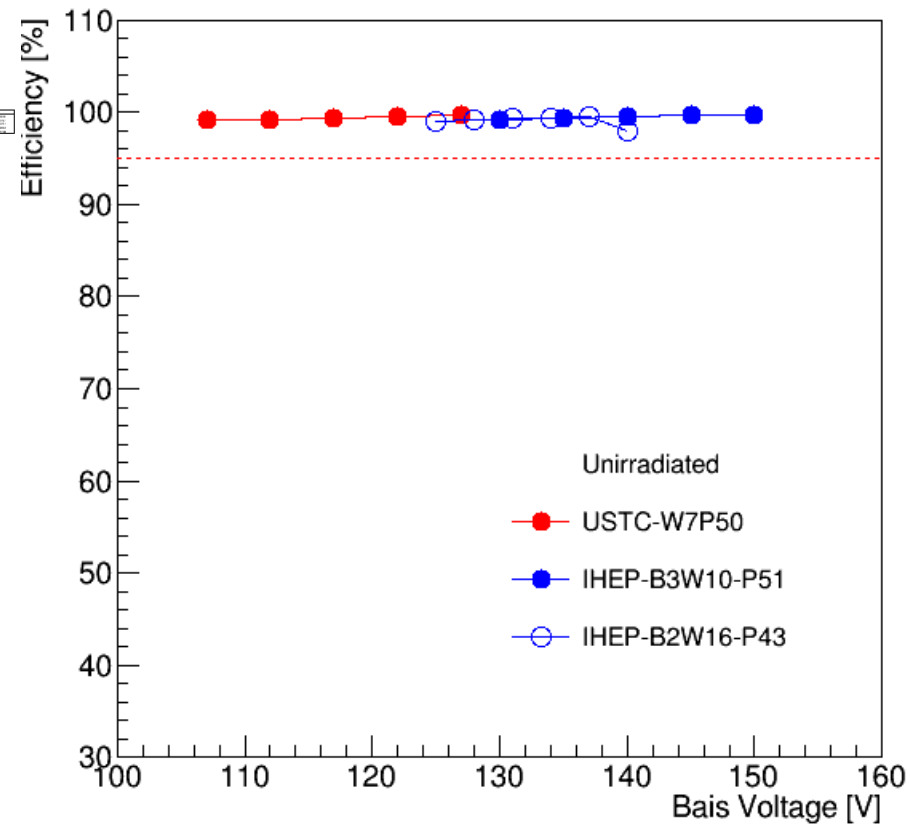
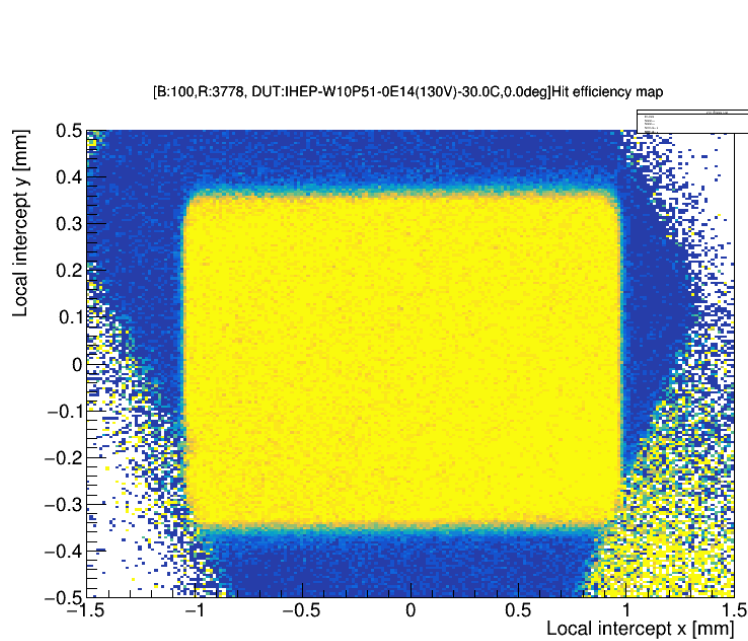


For ATLAS HGTD

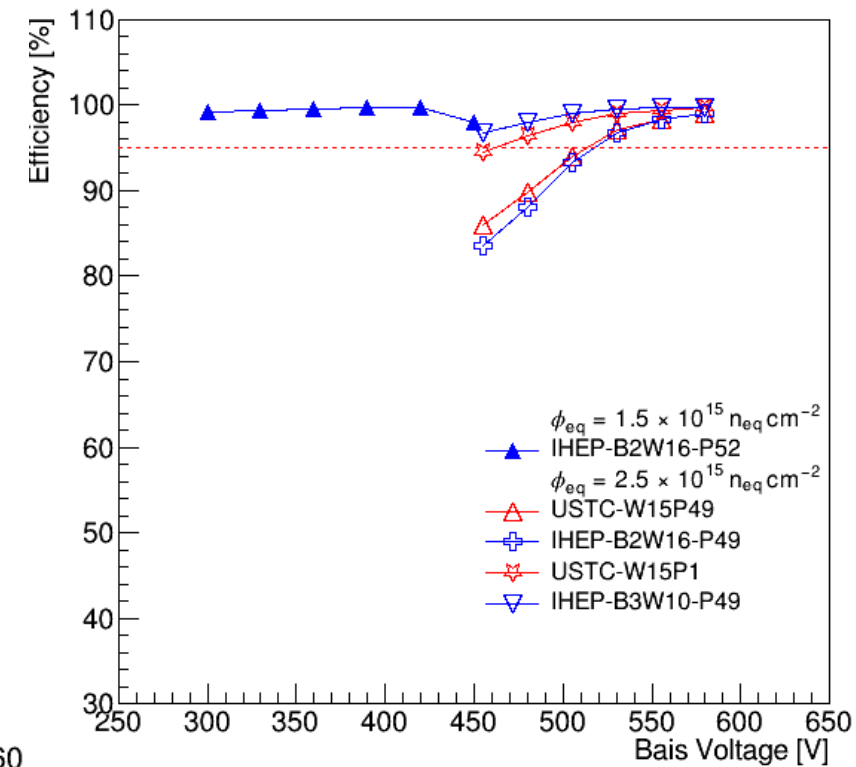


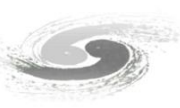
- Performance of pre-production sensors: Beam test results
- Efficiency : 95%~100% for sensors before and after irradiation, fulfills HGTD project requirement

Hit Efficiency - HGTD TB June 2024

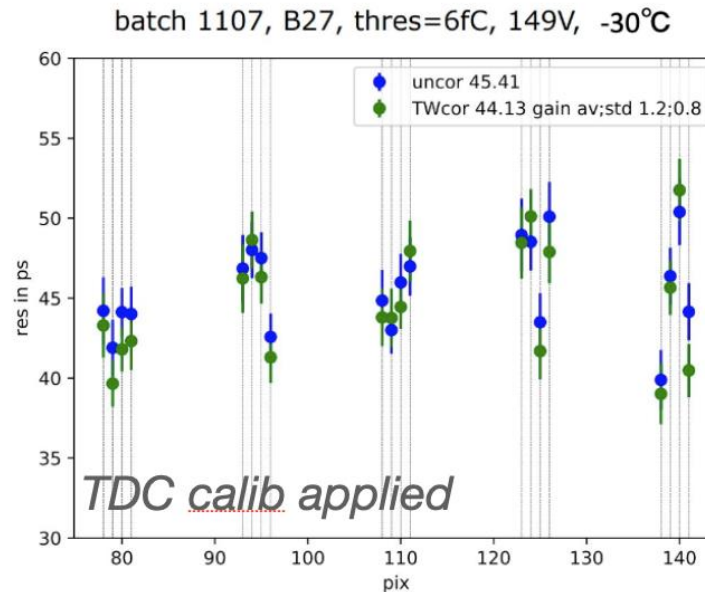
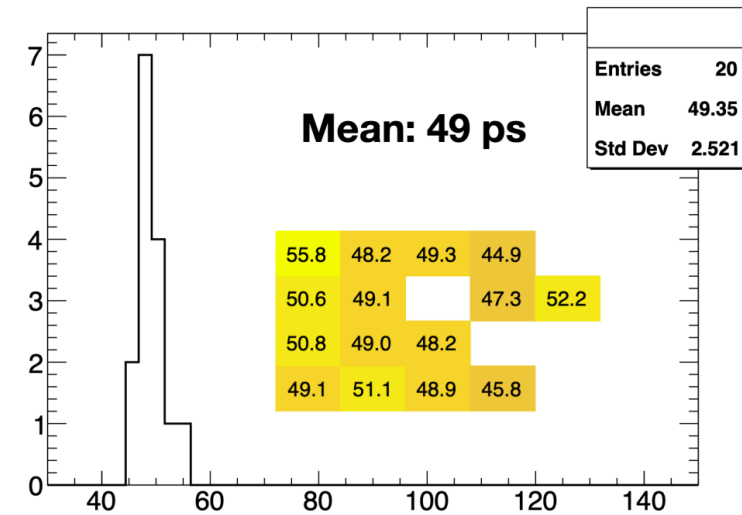
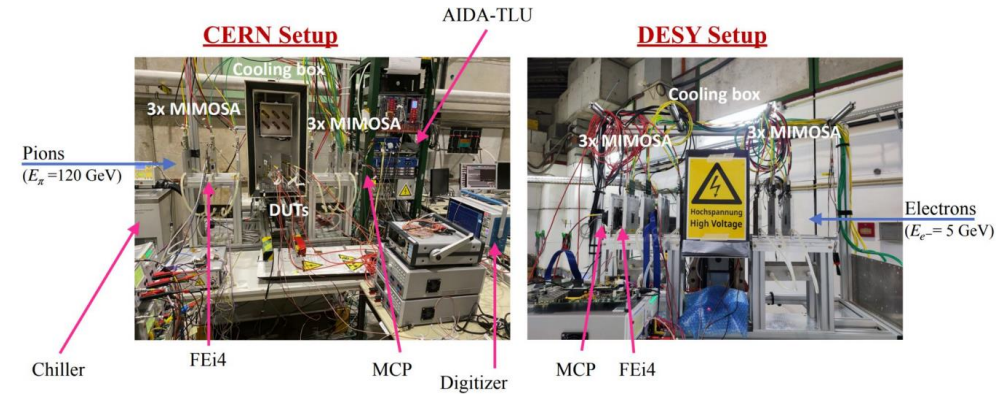
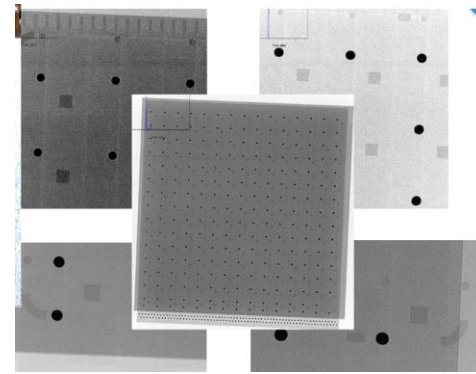


Hit Efficiency - HGTD TB June 2024

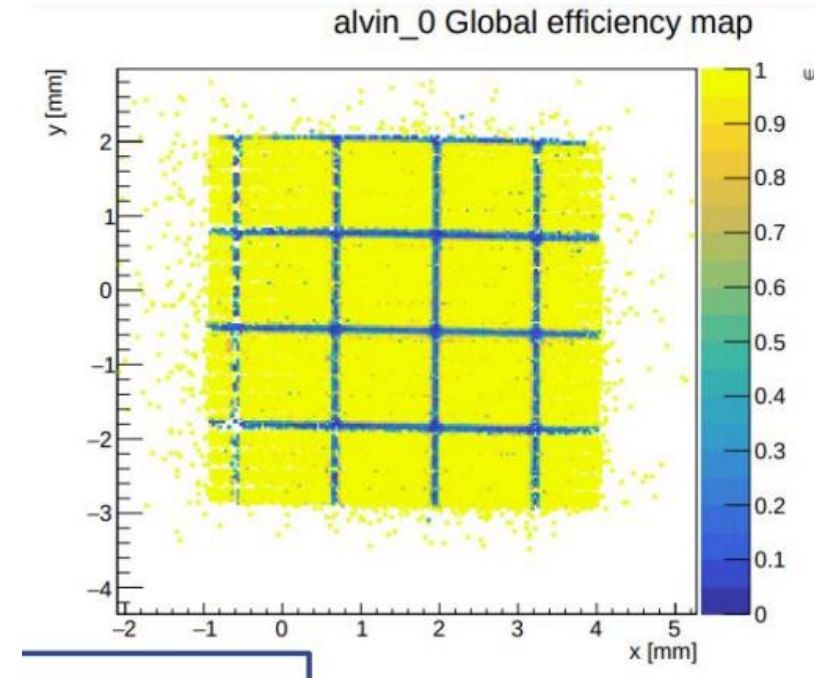


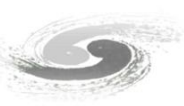


- IHEP Pre-production sensors with ASIC(Altiroc3): Beam test results
- Timing resolution can reach 50 ps for the sensor/ASIC module
- The efficiency is larger than 98%



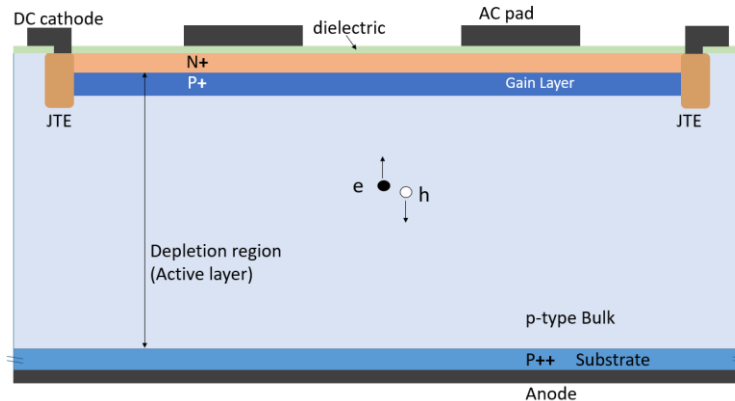
~45 ps after calibration and time walk correction





AC-LGAD development

- ◆ **AC-LGAD sensor is the choice for future collider OTK & TOF detector to provide both spatial resolution and timing resolution.**



- metal AC readout electrode and a thin dielectric layer (Si_3N_4 , SiO_2) above the N+ layer
- **Less dead area and better position resolution**
- Research institute: FBK, HPK, INFN, BNL, CNM, USTC, IHEP...

- Spatial resolution: 10 μm Time resolution: 30-50 ps

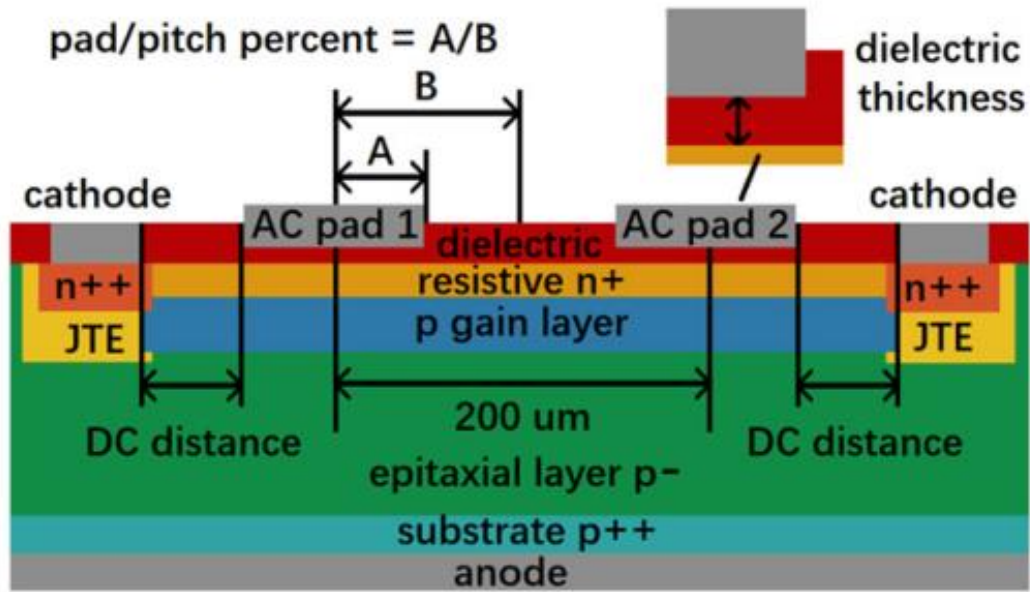


AC-LGAD R&D at IHEP

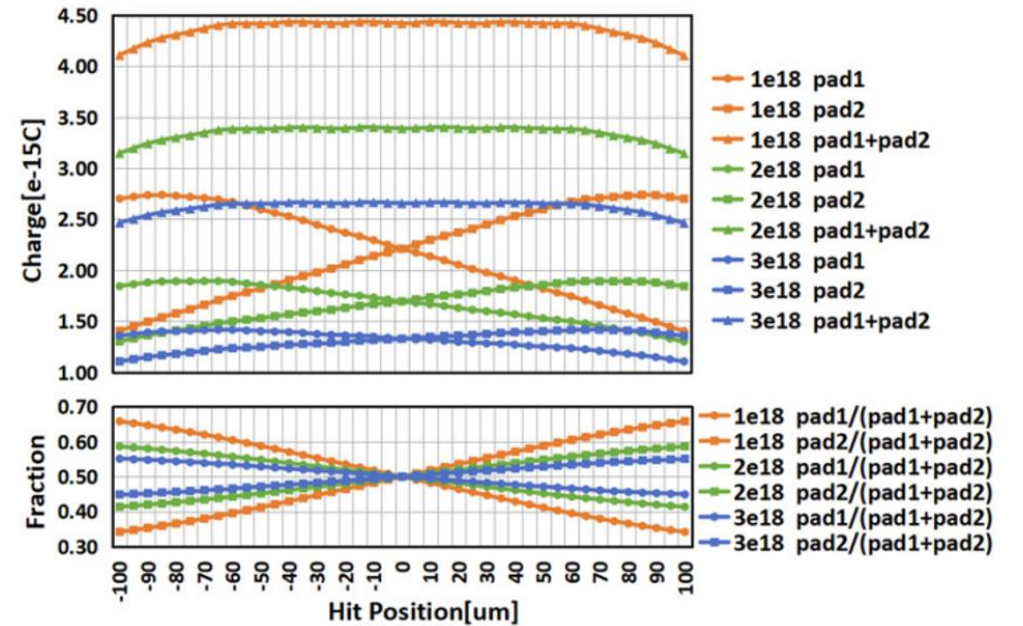
◆ AC-LGAD sensor simulation: Optimization of process and structure parameters

Process parameter: n+ layer dose, AC dielectric material and thickness

Structure parameter: pad shape, pad-pitch size



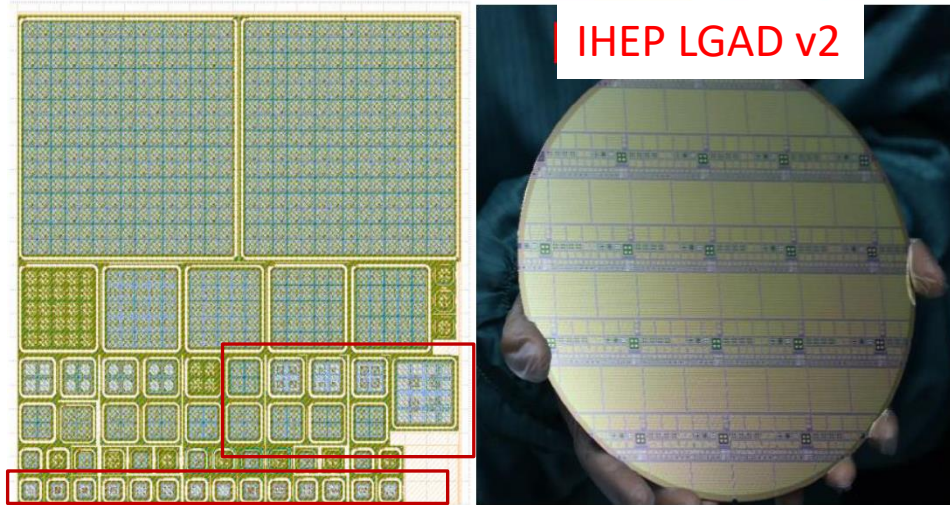
TCAD model of AC-LGAD for simulation



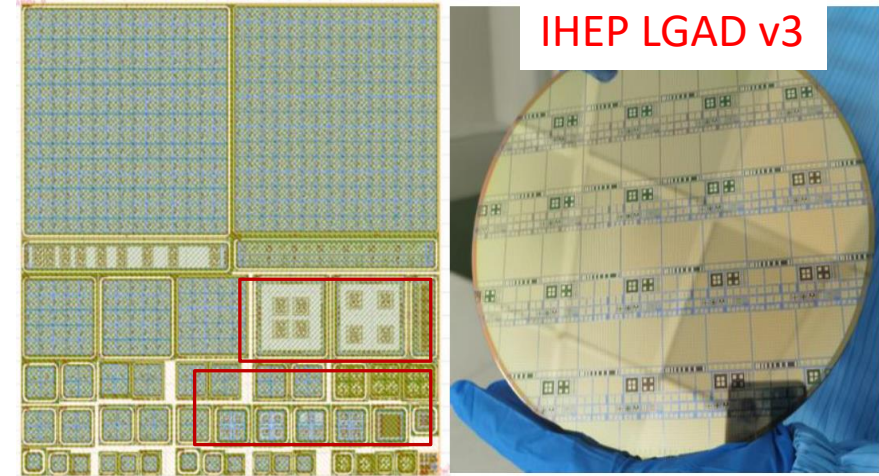
Lower n+ dose \rightarrow Large resistivity \rightarrow good spatial resolution

Design of AC-coupled low gain avalanche diodes (AC-LGADs): a 2D TCAD simulation study, JINST, 2022.9, DOI: [10.1088/1748-0221/17/09/C09014](https://doi.org/10.1088/1748-0221/17/09/C09014)

AC-LGAD R&D at IHEP



IHEP LGAD v2

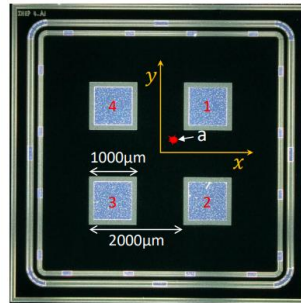


IHEP LGAD v3

AC-LGAD R&Dv1:

Pixelated AC-LGAD

- With different pad-pitch size
1000-2000um
100-500um
100-200um
50-100um
- wafers: with different n+ dose: 10P to 0.2P



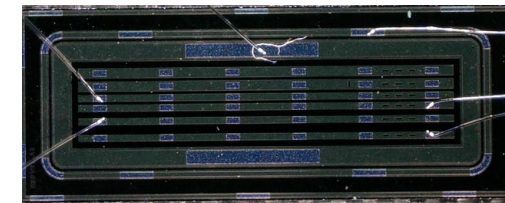
Process parameters(n+ dose) be studied.

The performance of large-pitch AC-LGAD with different N+ dose, Trans. Nucl. Sci. , 2023.6

AC-LGAD R&Dv2:

Pixelated and strip AC-LGAD

- With different pad-pitch size
1000-2000um pixel
100-250um strip
100-150um strip
50-100um strip
- wafers: with different n+ dose:0.2P to 0.01P



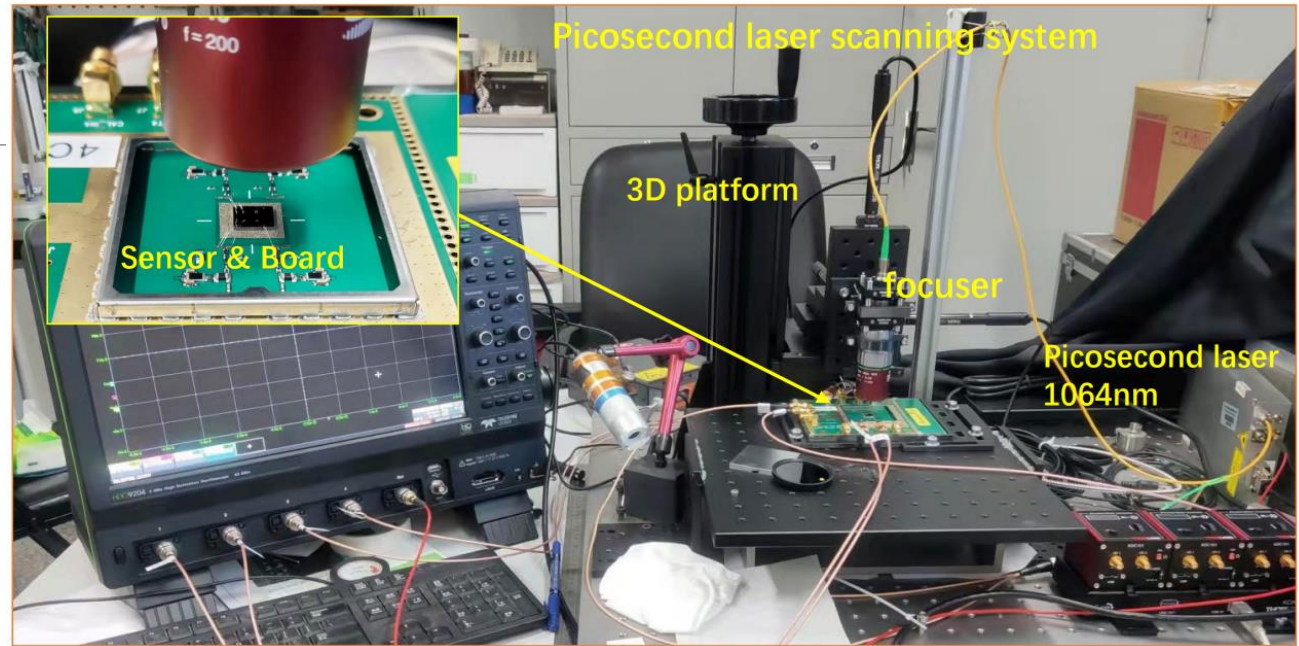
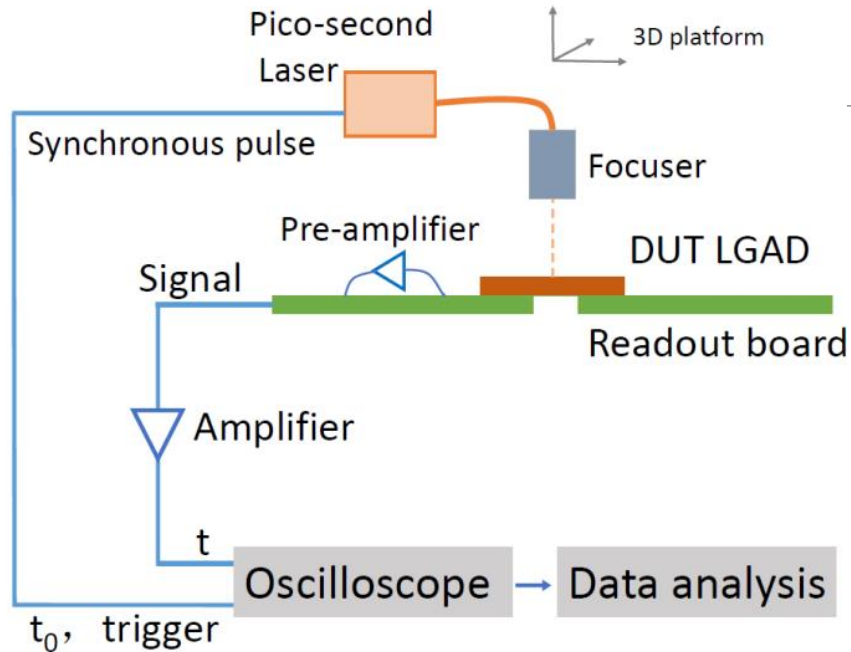
The performance of AC-coupled Strip LGAD developed by IHEP, NIMA, Volume 1062, May 2024, 169203



AC-LGAD testing setup

◆ AC-LGAD sensor testing system

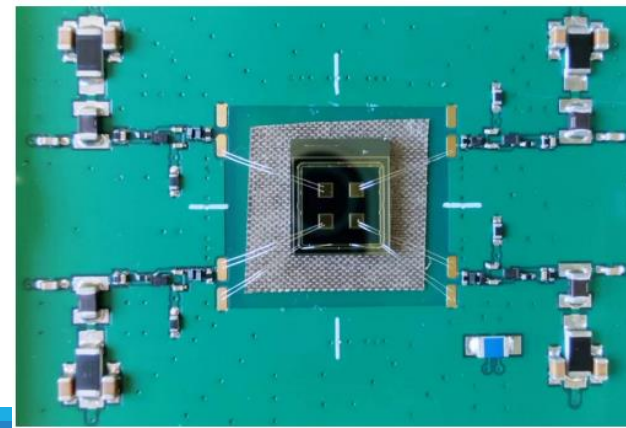
Pico-second laser testing system for AC-LGAD



4 channels readout board with fast amplifiers

Picosecond laser testing system

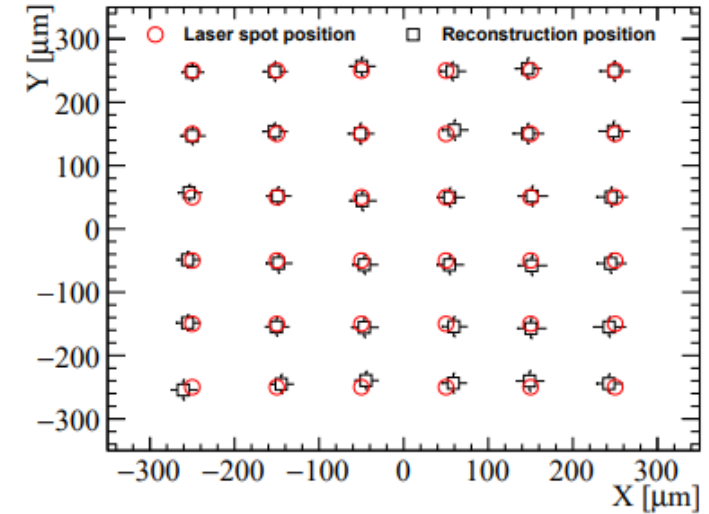
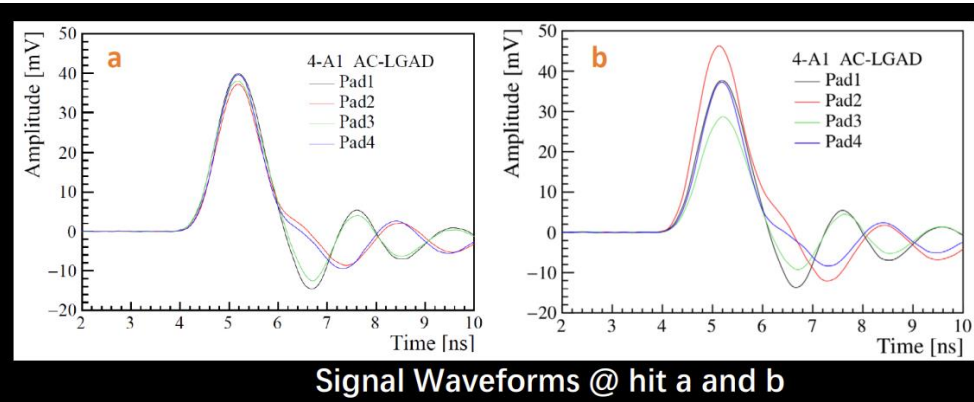
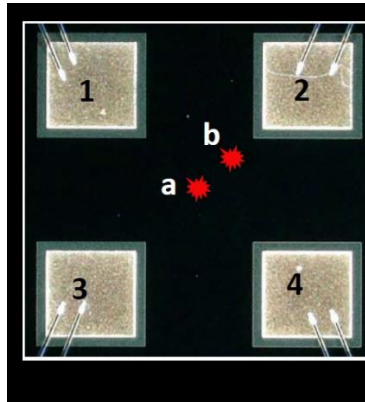
- Automated scanning
- Displacement accuracy: $1 \mu\text{m}$
- Picosecond laser: 1064nm
- Laser spot size: $2\sim 5 \mu\text{m}$



Position reconstruction, spatial resolution and timing performance of AC-LGAD be calculated based on the results from 4 pads.

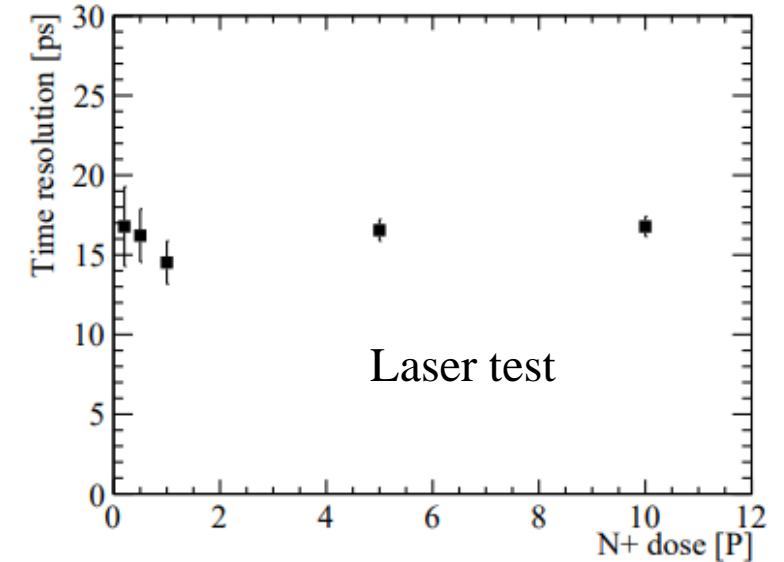
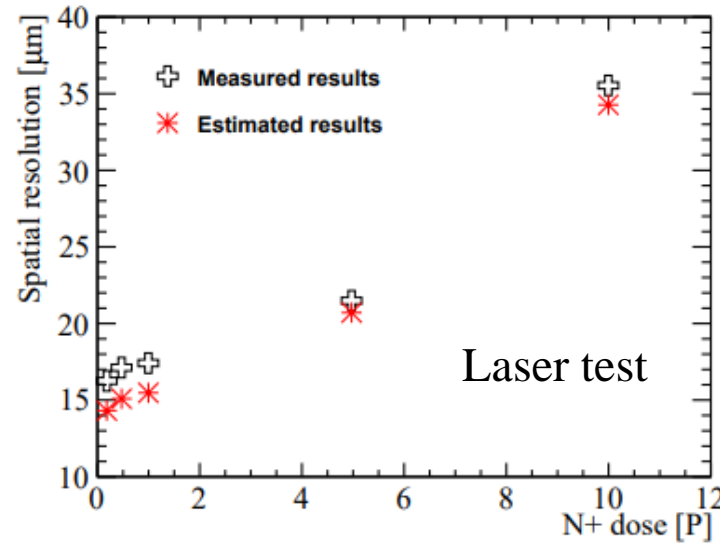
AC-LGAD development

Pixel size:
2000um
Pad size:
1000um

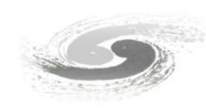


Pixelated AC-LGAD:

- Best spatial resolution ~15um (laser test)
- Timing resolution: 15-17ps
- N+ dose and other process parameters be studied.

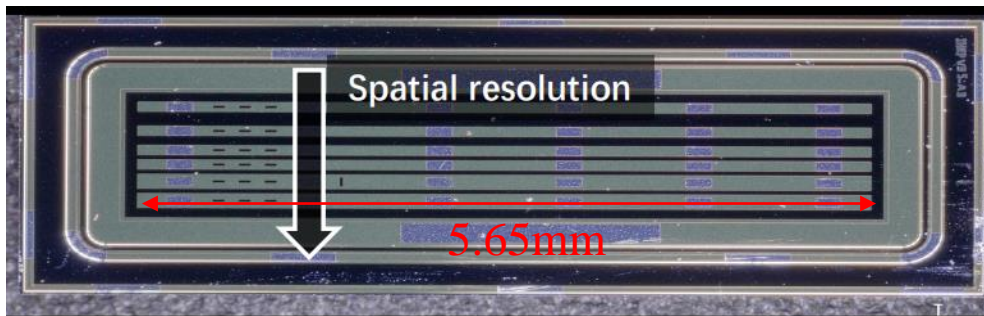


AC-LGAD development

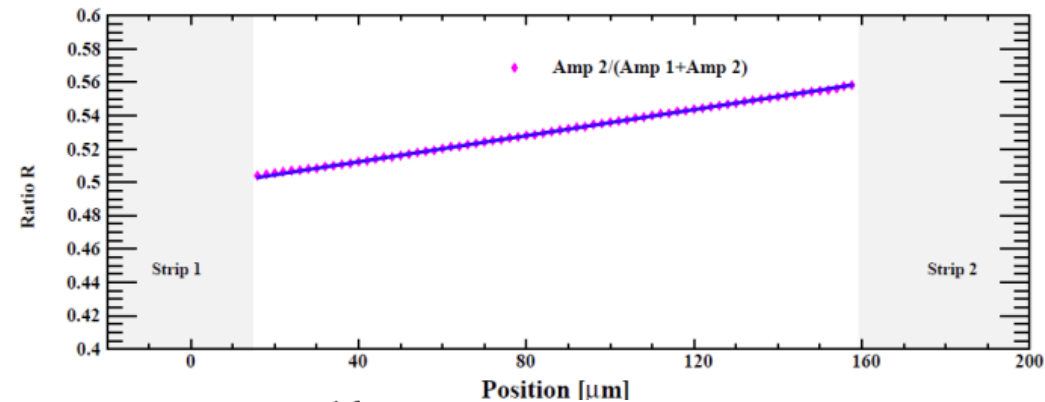


Spatial resolution: Laser testing

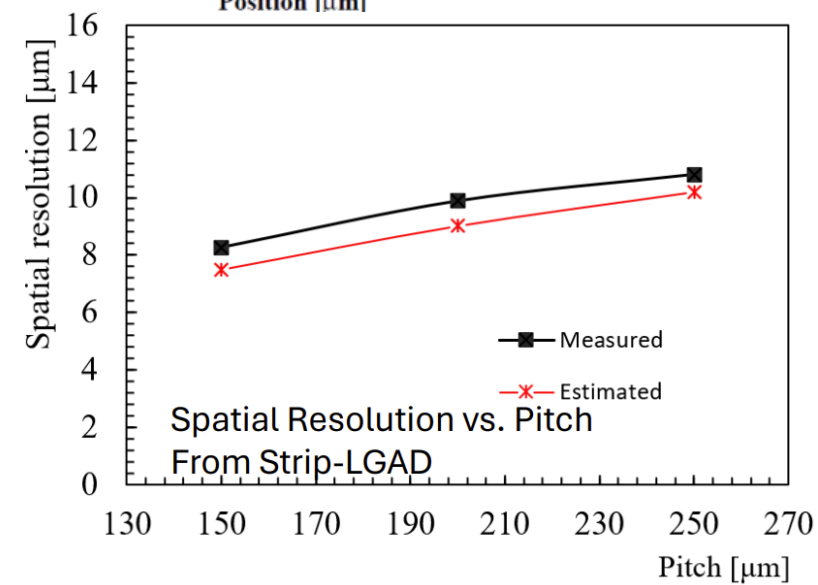
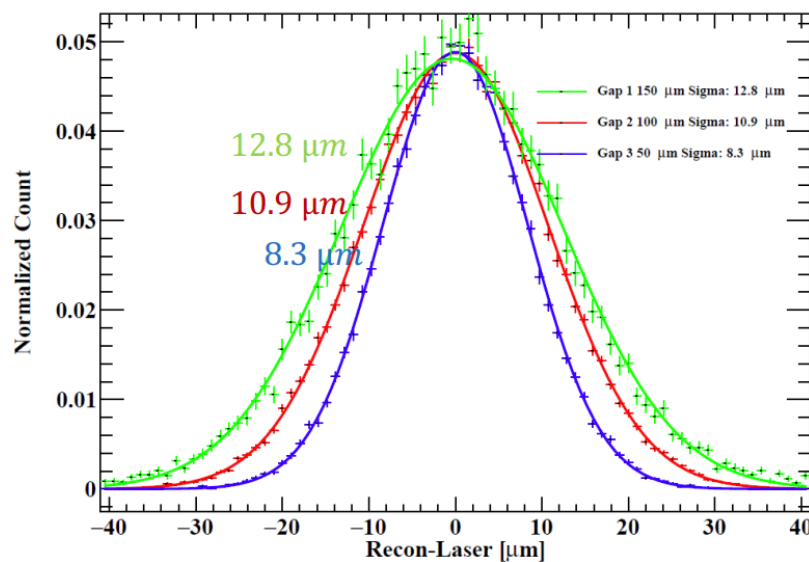
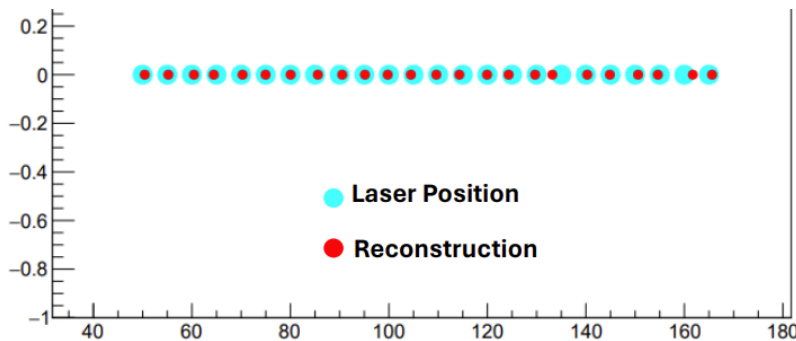
- Strip length 5.65mm
- pad-pitch size:
100-250 μm
100-200 μm
100-150 μm



Amplitude information



Position reconstruction



AC-LGAD with Pitch as 150 μm : Best spatial resolution~8 μm
(laser test)

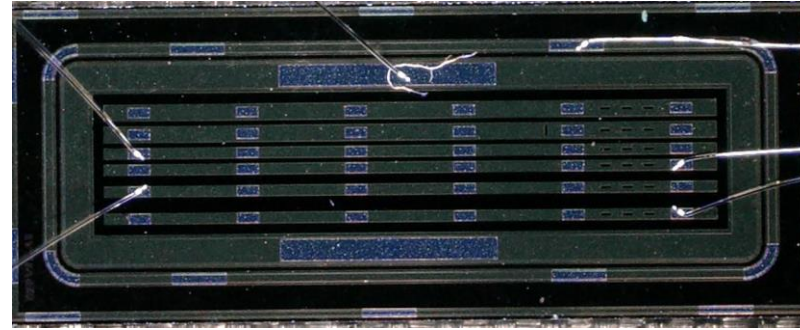
The performance of AC-coupled Strip LGAD developed by IHEP, NIMA, Volume 1062, May 2024, 169203

AC-LGAD development

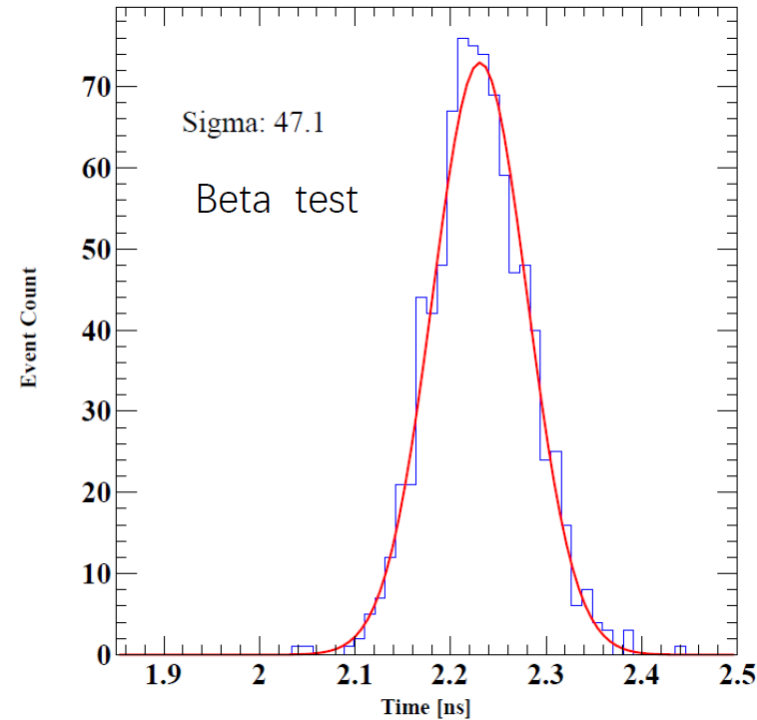
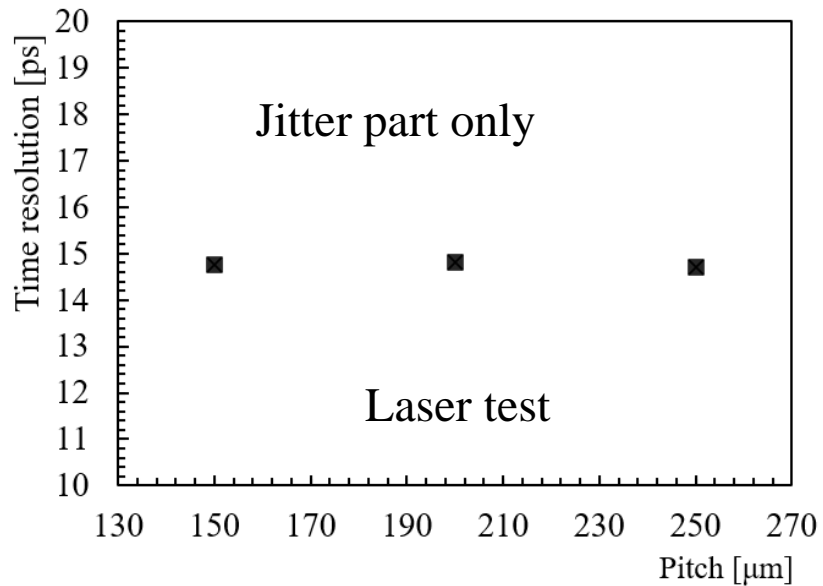


Timing resolution

$$\sigma_t^2 = \sigma_{TimeWalk}^2 + \sigma_{Landau}^2 + \sigma_{Jitter}^2$$



- Strip length 5.6mm
- pad-pitch size:
 - 100-250 μm
 - 100-200 μm
 - 100-150 μm



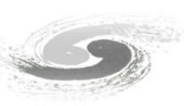
Landau and jitter contribution

$$\sigma_{AC-LGADStrip} = \sqrt{\sigma_{\Delta T}^2 - \sigma_{Trigger}^2}$$

Trigger: 28.5ps

The time resolution does not change significantly, ~15-17 ps.

Time resolution: 37.5 ps



LGAD application for X-ray detection



LGAD for X-ray detection

Advantage:

- Low Gain Avalanche detector could improve signal-to-noise for soft x-ray sensors, with good spatial resolution
- In photon science, the gain provided by LGAD sensors can **boost the signal-to-noise ratio of the detector system**, effectively **reducing the x-ray energy threshold** of photon counting detectors and the minimum x-ray energy where single photon resolution is achieved in charge integrating detectors.
- This can improve the hybrid pixel and strip detectors for soft and tender x-rays by **only changing the sensor element of the detector system**.

Research institute and status

PSI, Diamond, IHEP, USP, UCSC, SLAC and SINTEF..
 Foundry: CNM, FBK, HPK...

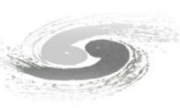
Low energy: 250eV, fast timing:<100ps

PSI: Development of LGAD sensors with a thin entrance window for soft X-ray detection
 a game changer for several resonant diffraction and spectromicroscopy applications.
 LGAD could be used for soft X-rays experiments at XFELs in combination with a CI readout, improving the single photon resolution

Low Gain Avalanche Diode Sensors for Time Resolved Synchrotron Applications
 Diamond:

- exploit the circa-100-ps timing capability of the Timepix4+LGAD to perform highly time-resolved experiments;
- an LGAD sensor to couple to a hybrid such as the Timepix4 to image X-rays at energies as low as 250 eV by making use of the sensor's built-in amplification.

LGAD design for X-ray



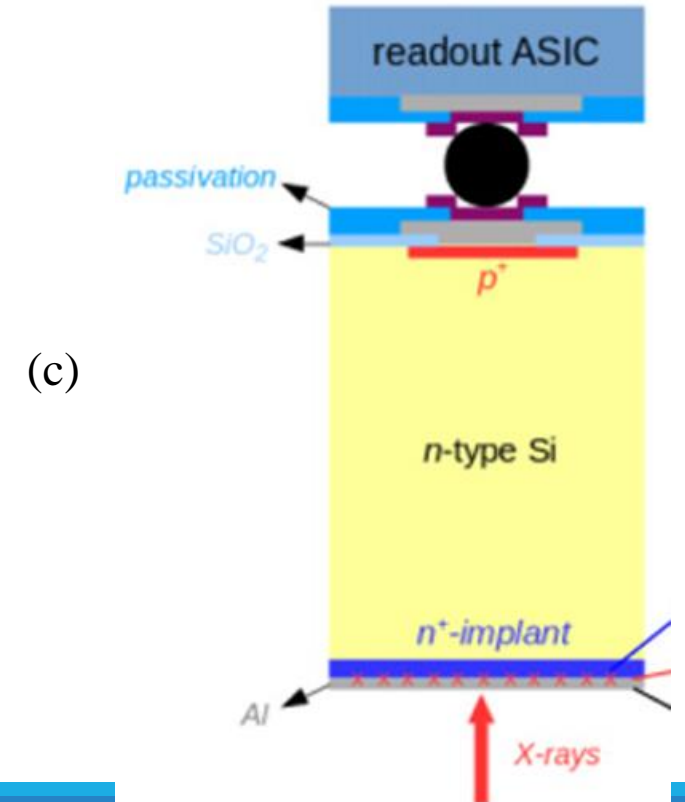
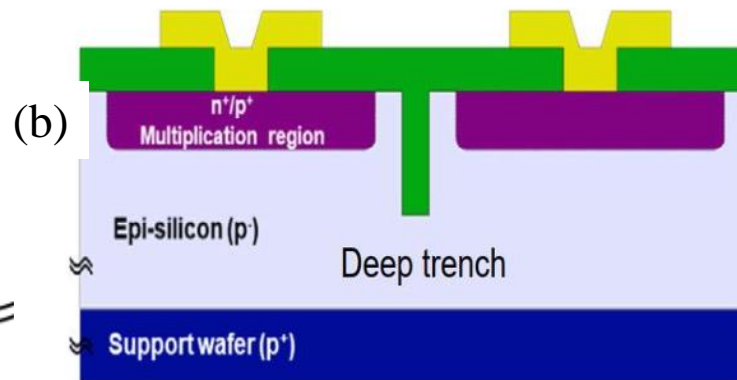
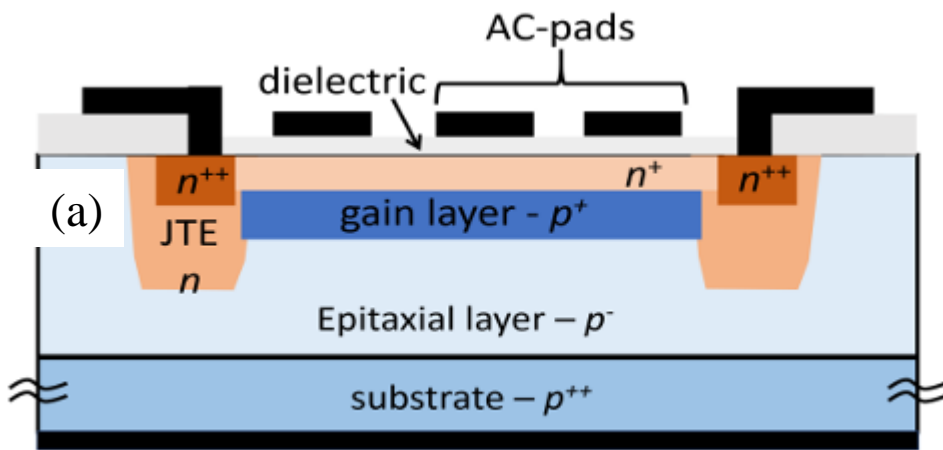
➤ For X-ray detection:

LGAD structures need to be optimized for several aspects relevant to photon science applications.

- The placement of the gain structure on quantum efficiency, the active thickness
- The sensors' signal characteristics and its compatibility with available readout chips

➤ For 50-100um pixel size X-ray image application: small pixel size with good fill factor

- AC-coupled LGAD, trench-isolated LGADs(Ti-LGAD), inversed LGADs
- Its compatibility with available readout chips also need to be considered.



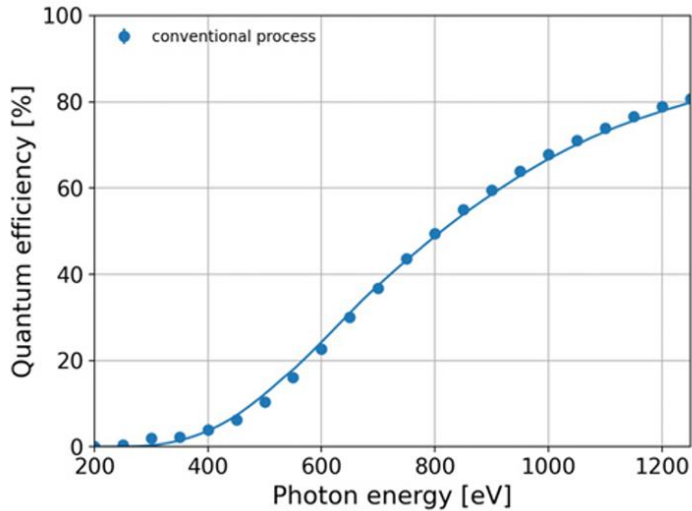
LGAD design for X-ray



➤ For X-ray detection:

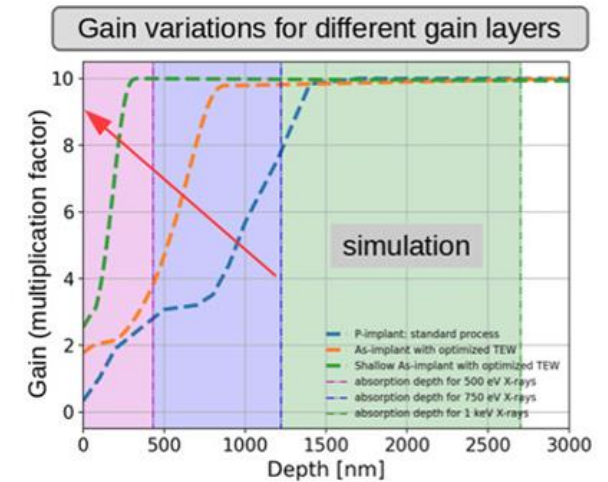
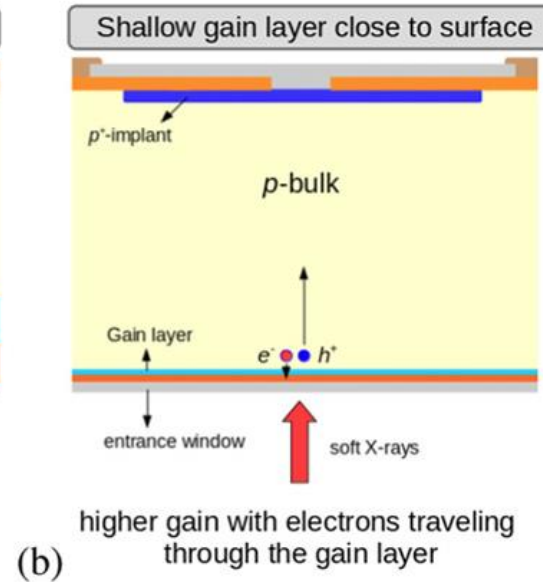
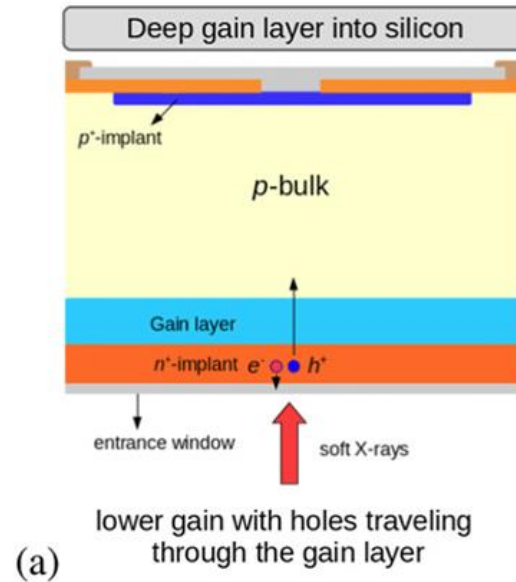
- For low energy X-ray detection, the conventional LGAD structure is not compatible with thin-entrance window (<50nm).

Inversed LGAD with thin-entrance window



The measured (dots) and simulated (line) QE for a conventional silicon sensor

At 400eV the QE is less than 5%



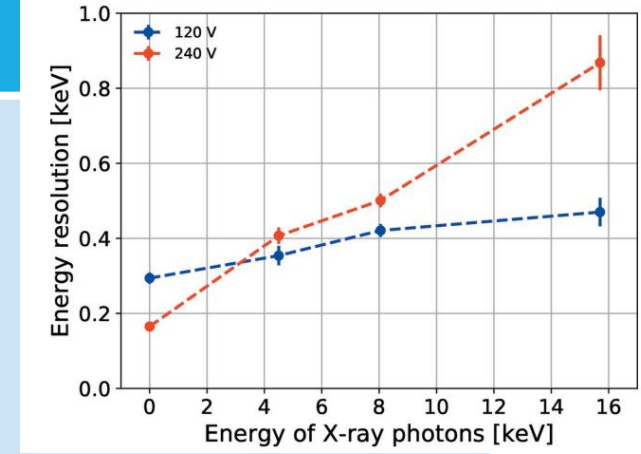
PSI: Development of LGAD sensors with a thin entrance window for soft X-ray detection

LGAD testing results (X-ray)



Institute	Sensors type	X-ray source	performance
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PSI, FBK	FBK(50um)	X-ray energy range (2–4 keV) installed at the PHOENIX beamline of the Swiss Light Source	The average energy resolution for all channels at 2.1 keV is 0.310 ± 0.024 keV RMS.
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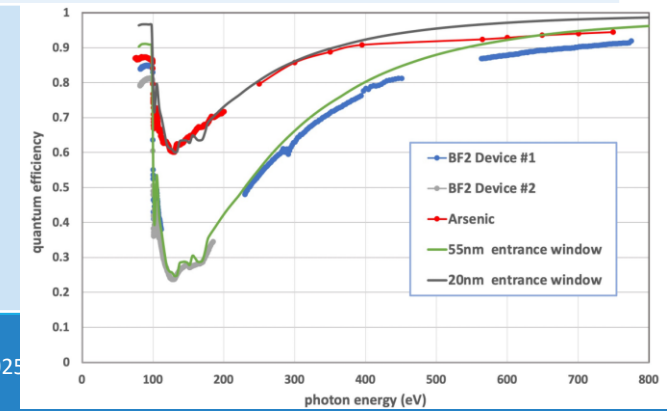


USP, UCSC	HPK LGAD type 3.1, type 3.2 (50um) BNL LGAD (20um)	Stanford Synchrotron Radiation Light source SSRL 11-2 beamline	More details in Marco's talk next
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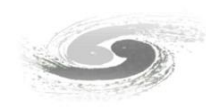
For 35 keV X-ray:

	HPK PIN	HPK3.1		HPK3.2		BNL 20um	
Bias V	200 V	150 V	230 V	80 V	130 V	50 V	100 V
Energy Resolution	14 %	6 %	17 %	10 %	20 %	6 %	16 %
Energy Response	19 mV	75 mV	185 mV	68 mV	211 mV	66 mV	147 mV
σ_t CFD	78 ps	141 ps	123 ps	371 ps	171 ps	69 ps	65 ps

SLAC, SINTEF (HSTD 13) free electron lasers, SLAC's LCLS-II	New Thin-Entrance window LGAD	Not tested yet	QE simulation gain = 7.0
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LGAD testing results(X-ray)

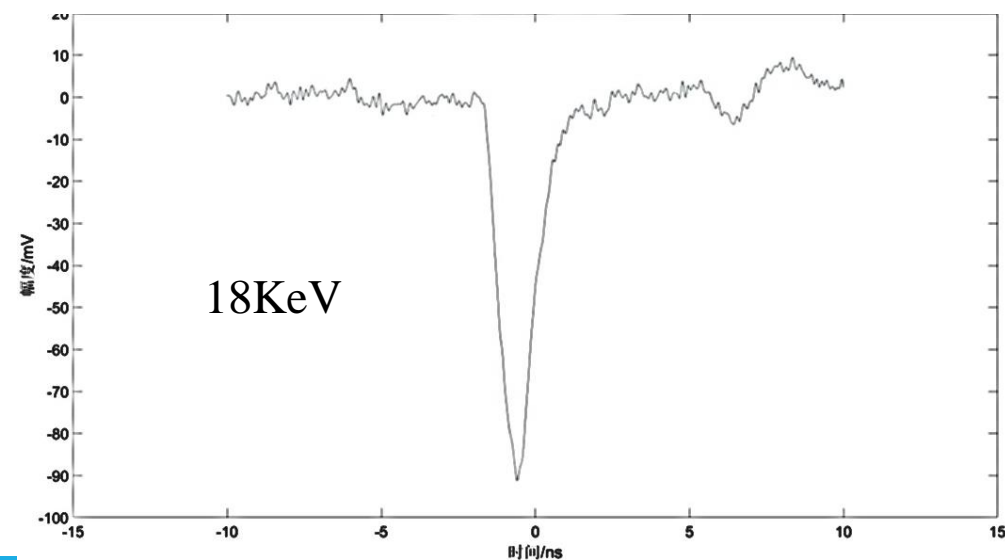
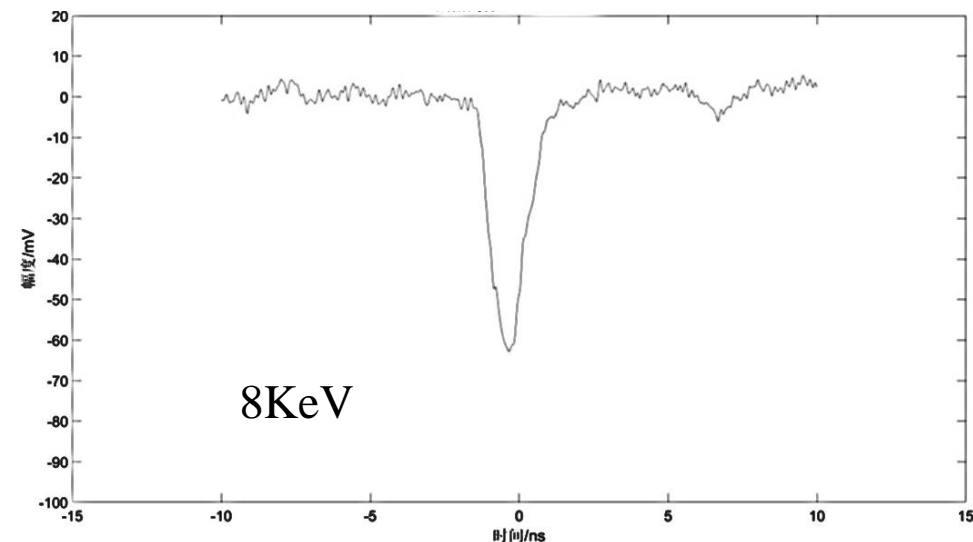


Sensor type: IHEP LGAD version3 sensors: W25

	size	capacitance	Active thickness
Single LGAD	1.3mm x 1.3mm	4.2pF	80um

Sensor be wire bonded to readout board,
gain of readout board(two stage amplifiers): 100.
X-ray source at BSRF be used for testing.

	X-ray energy	Noise (RMS)	Signal amp mV	Rise time
Single LGAD	8KeV	2.8mV	70	1.2ns
	18KeV		70-130	0.9ns





LGAD design (for X-ray)

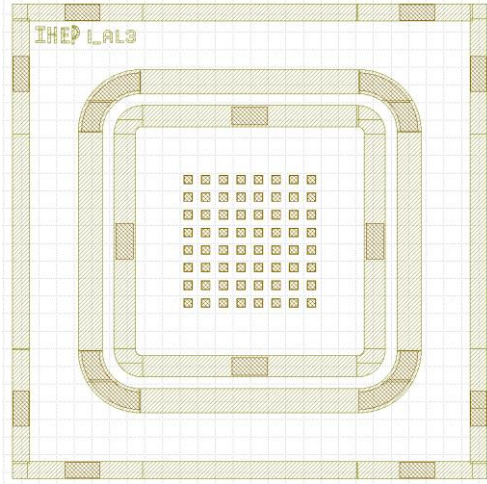
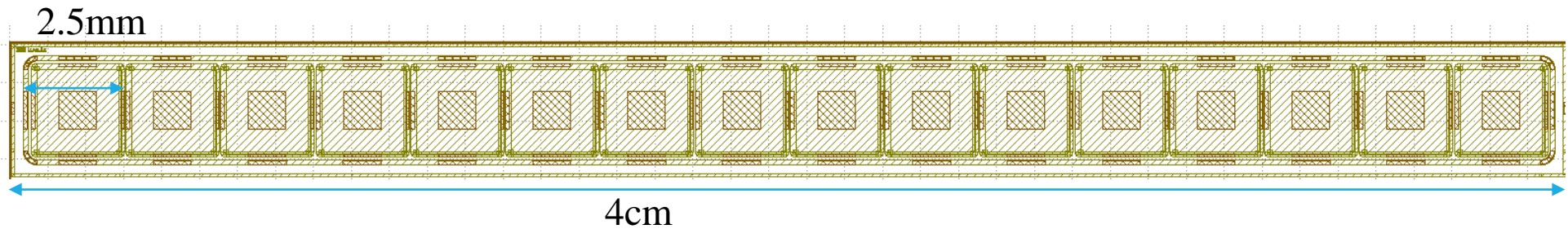
New run be submitted, sensors be finished mid of this year.

AC-LGAD:

DC-LGAD:

	Pixel size	Active thickness
Single LGAD	1.3mm x 1.3mm	50um 80um 300um
1x16 LGAD	2.5mm x 2.5mm	50um 80um 300um

	Pixel size	Pixel array	Active thickness
LGAD 55	55um x 55um	5x5	50um 80um 300um
LGAD 100	100um x 100um	8x8	50um 80um 300um



Check the basic performance of LGAD for X-ray detection.
 More simulation and design need to be done to optimize LGAD structures for X-ray application.



Summary

- **DC-LGAD** has timing resolution $<35\text{ps}$, be chosen as timing detector to solve pile-up issues for ATLAS HGTD project. Now IHEP LGAD sensors' pre-production is finished, and sensors fulfill the project requirement. PRR Review passed and final production started.
- **IHEP AC-LGAD** R&D chip has been designed and studied. Spatial resolution: $<10\mu\text{m}$, timing resolution: $<40\text{ps}$
- **LGAD has potential for X-ray detection** due to its good timing performance and S/N advantage for low energy x-ray, be studied by many light sources.
- **Studies need to be done to optimize the LGAD sensor performance, make it more suitable for X-ray application.** (Simulation, design, fabrication, testing, readout board and ASIC, bonding...)

Small pixel size, efficiency, low energy \rightarrow new design of AC-LGAD and inversed LGAD

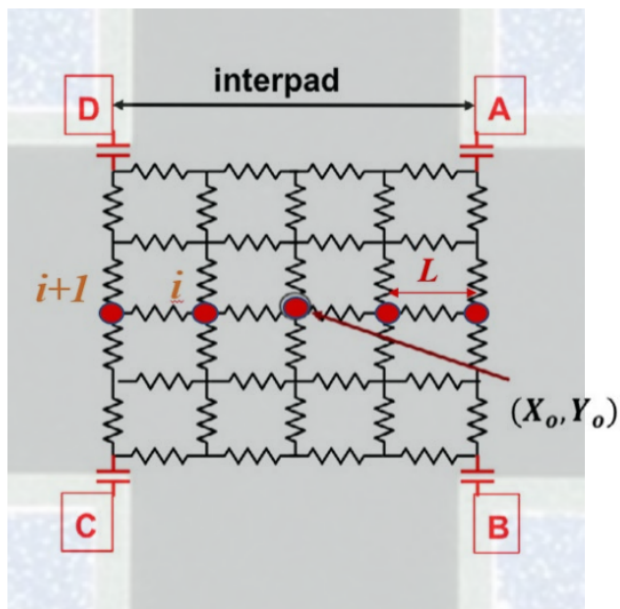
Sensor bonding with ASIC, its performance

Collaboration is warmly welcome.

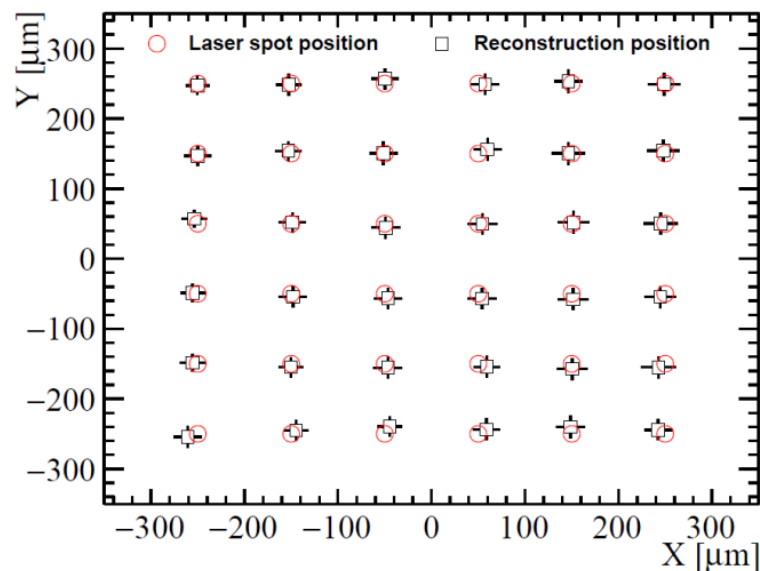
Mei Zhao, zhaomei@ihep.ac.cn

Backup

ASIC: [TWEPP 2024 Topical Workshop on Electronics for Particle Physics \(30 September 2024 - 4 October 2024\): An ASIC for ToF-PET application with MCP-PMTs · Indico](#)

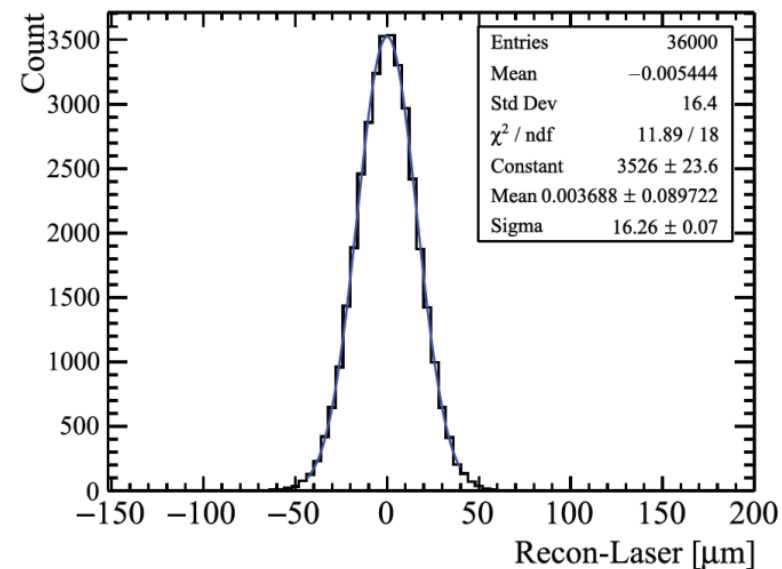


reconstructed 6x6 positions



Good consistency

Spatial resolution: reconstruction - laser



$$X = X_0 + k_x \left(\frac{q_A + q_B - q_C - q_D}{q_A + q_B + q_C + q_D} \right) = X_0 + k_x m$$

$$Y = Y_0 + k_y \left(\frac{q_A + q_D - q_B - q_C}{q_A + q_B + q_C + q_D} \right) = Y_0 + k_y n$$

Correction factor: k_x k_y

$$k_x = L \frac{\sum(m_{i+1} - m_i)}{\sum(m_{i+1} - m_i)^2} \quad k_y = L \frac{\sum(n_{i+1} - n_i)}{\sum(n_{i+1} - n_i)^2}$$

**Discretized
Positioning
Circuit model
(DPC)**

Spatial resolution :

- the sigma of the difference between the laser and the reconstructed position

$$\sigma_{\text{spatial}} = \sigma_{\text{reconstruction-laser}}$$

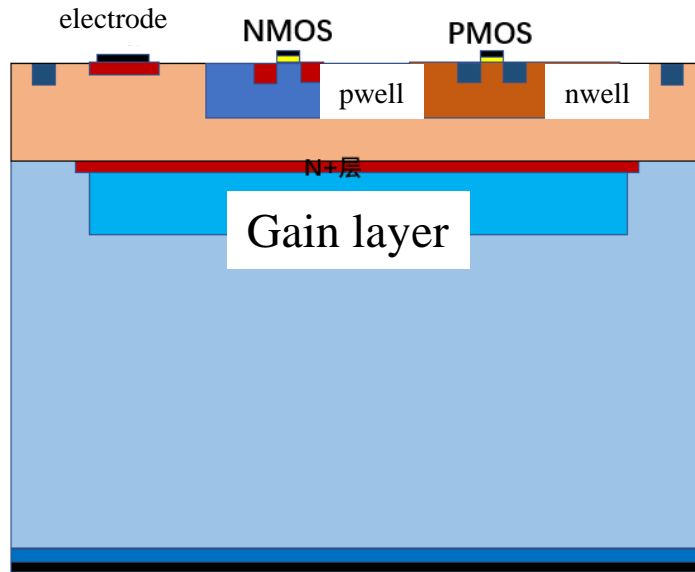
Discretized Positioning Circuit model
Machine learning method ongoing



Monolithic LGAD

➤ Monolithic LGAD: Fermilab, University of Geneva, CERN, INFN, CNM, FBK...

MAPS detector timing information: 10ns → < 50ps Bonding cost, and also material budget reducing



EPI layer
Electronic circuit

LGAD sensor
for charge
multiplication
and sensing

Backside p+ layer, metal

Monolithic silicon sensors with very high time resolution will enable making 4D measurements better and in a single and cost-effective silicon tracker, and will also influence how future particle-physics experiments will be designed and constructed.

---G. Iacobucci et al 2022 JINST 17 P10040

➤ Monolithic LGAD:

	sites	node	Pixel size	Timing
MonPicoAD	University of Geneva, CERN	130nm SiGe	25x25 μm^2	25ps
miniCACTUS	IRFU, IFAE	150nm Si	0.5x1 mm^2	65ps
Madpix	INFN	110nm Si	250 x 100 μm^2	75ps